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## **AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) An interleaving management method for upgrading a data processing speed of a flash memory, comprising a plurality of flash memory cells, wherein each of said flash memory cells comprises a plurality of blocks for reading and writing data and a plurality of pages in each said blocks, the method comprising:

continuously writing data into said plurality of flash memory cells, wherein when writing two or more sets of sectors into said plurality of flash memory cells, write a first sector into a first flash memory cell, and while the process of writing said first sector into said first flash memory cell is ongoing, a second flash memory cell is enabled so that a second sector can be written into said second flash memory cell;

wherein the step of writing one of the sectors into one page of one of the blocks includes:

defining the one of the blocks as a mother block;

selecting a backup block as a child block;

assigning the child block a logical address same as a logical address of the mother block;

reading out a plurality of pages prior to the one page into which the sector to be written

from the mother block and writing the plurality of pages prior to the one page into the child

block; and

writing the one of the sectors into the one page.

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2. (Currently Amended) The interleaving management method according to claim 1,

wherein said a-plurality of flash memory cells for continuously writing data continuously are

arranged in an interleave structure.

3. (Currently Amended) The interleaving management method according to claim 1,

wherein said plurality of flash memory cells is used in a mother and child structure, said mother

and child structure possessing two physical features constitute one logical address, so that for

writing data, transferring and erasing steps in said flash memory cells can be avoided, thus a life

time of said flash memory cells can be extended and also data processing speed of said flash

memory cells can be increased wherein the step of writing the one of the sectors into the one

page includes:

when the one of the sectors is not a last set of the data, writing a next sector of the data

into a page of the child block immediately following the one page;

erasing the mother block after writing a last sector of the data into the child block.

4. (Currently Amended) The interleaving management method according to claim 2,

wherein said flash memory cells are arranged in a group constituting the interleaving structure

supporting a copy back command, correspondingly using copy back command, wherein a 64 mb

flash memory cell is divided into four zones, each zone has 1024 blocks and each block has 32

pages, and four 64 mb flash memory cells constituting said interleaving structure comprises 4

zones, wherein each zone has 1024 blocks and each block has 128 pages.

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5. (Currently Amended) The interleaving management method according to claim 1, wherein said interleaving management method for managing data processing of a plurality of flash memory cells is suitably applied in a hosting device, wherein said hosting device comprises, includes at least one of a portable ROM, a card reader in USB1.1 series, or a portable ROM, a card reader in USB2.0 series, or and an IDE/PCMCIA interface.